

IN THE CLAIMS:

Please amend claims 1 and 2 as follows.

1. (currently amended) A method for manufacturing MTJ cell of MRAM comprising:
forming a metal layer for connection layer connected to a semiconductor substrate
through a lower insulating layer;
forming a pinned magnetic layer on the metal layer;
physically impacting a surface of the pinned magnetic layer with an atom to form an
amorphous layer thereon, so as to increase the uniformity of the pinned magnetic layer;
sequentially forming a tunneling barrier layer, a free magnetic layer and a MTJ capping
layer on the amorphous layer; and
patterning the MTJ capping layer, the free magnetic layer, the tunneling barrier layer,
amorphous layer and the pinned magnetic layer using a MTJ cell mask to form a MTJ cell.
2. (currently amended) The method according to claim 1, wherein the atom is selected
from the group consisting of P ~~[[øø]]~~ and As.